WAFER PROCESSING METHOD

ABSTRACT

Disclosed herein is a wafer processing method including: a protective film forming step of applying a liquid resin to the front side of a wafer to form a protective film; a protective tape adhering step of adhering a protective tape to a surface of the protective film; a modified layer forming step of applying a laser beam having such a wavelength as to be transmitted through the wafer to the wafer along each of division lines, with a focal point positioned inside the wafer, to form a modified layer inside the wafer along each of the division lines; and a back side grinding step of grinding the back side of the wafer while supplying grinding water to thin the wafer to a predetermined thickness and to crack the wafer along the division lines using the modified layers as crack starting points so as to divide the wafer into individual device chips, after the protective film forming step, the protective tape adhering step, and the modified layer forming step are carried out.

(Fig. 10B)